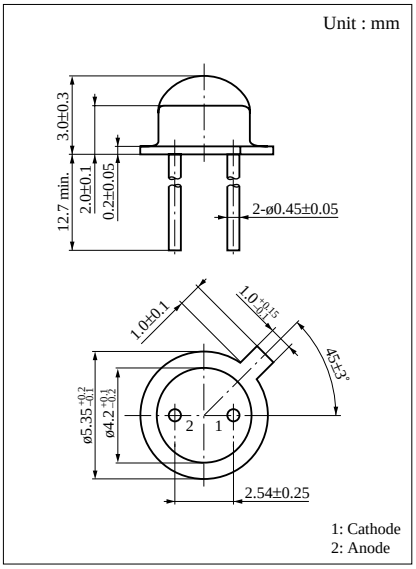
LN52

GaAs Infrared Light Emitting Diode

For optical control systems



Features

- High-power output, high-efficiency : P_O = 6 mW (typ.)
- Wide directivity, matched for external optical systems : θ = 100 deg.
- Infrared light emission close to monochromatic light : λ_P = 950 nm
- Optimum for mesuring instruments and control equipments in conbination with silicon photodetectors

Absolute Maximum Ratings (Ta = 25˚C)

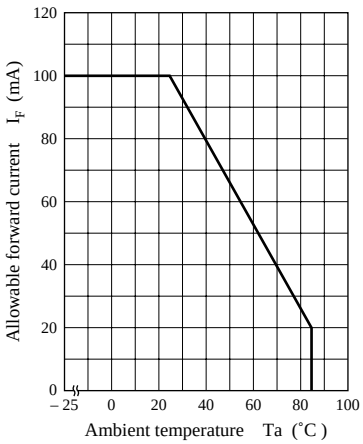
Parameter	Symbol	Ratings	Unit
Power dissipation	P_D	160	mW
Forward current (DC)	I_F	100	mA
Pulse forward current	I_{FP}*	2	A
Reverse voltage (DC)	V_R	3	V
Operating ambient temperature	T_{opr}	–25 to +85	˚C
Storage temperature	T_{stg}	–30 to +100	˚C

* f = 100 Hz, Duty cycle = 0.1 %

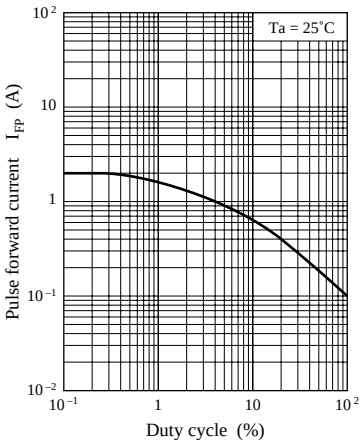
Electro-Optical Characteristics (Ta = 25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Radiant power	P_O	I_F = 100mA	3.5	6		mW
Peak emission wavelength	λ_P	I_F = 100mA		950		nm
Spectral half band width	$\Delta\lambda$	I_F = 100mA		50		nm
Forward voltage (DC)	V_F	I_F = 100mA		1.25	1.6	V
Reverse current (DC)	I_R	V_R = 3V			10	μA
Capacitance between pins	C_t	V_R = 0V, f = 1MHz		50		pF
Rise time	t_r	I_{FP} = 100mA		1		μs
Fall time	t_f			1		μs
Half-power angle	θ	The angle in which radiant intencity is 50%		100		deg.

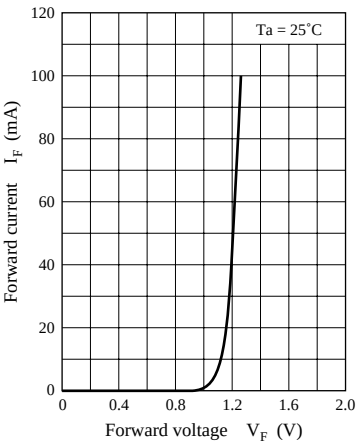
I_F — Ta



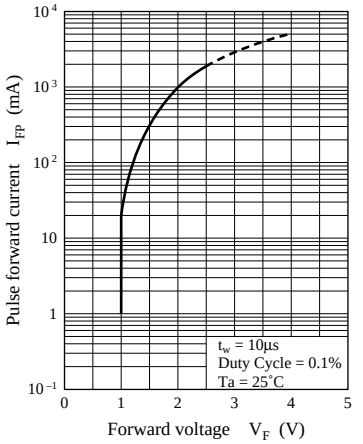
I_{FP} — Duty cycle



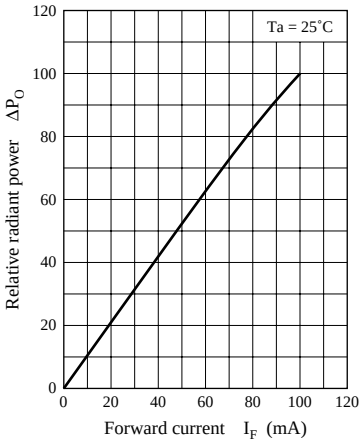
I_F — V_F



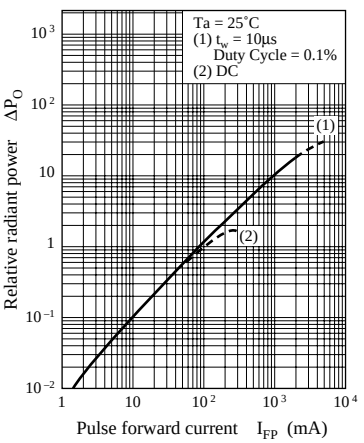
I_{FP} — V_F



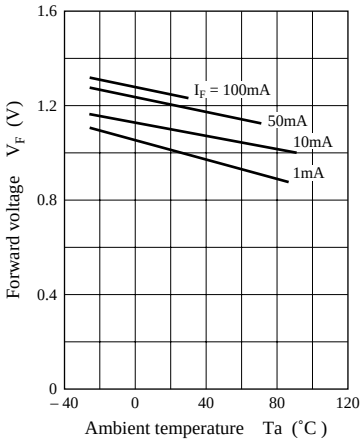
ΔP_O — I_F



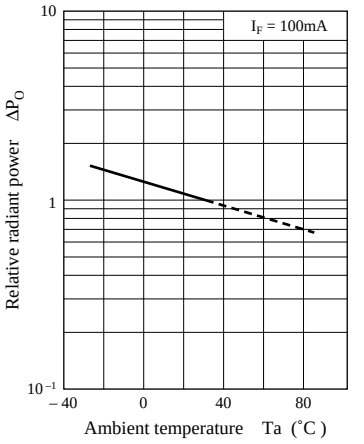
ΔP_O — I_{FP}



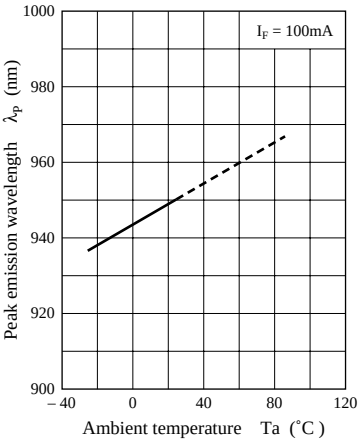
V_F — Ta



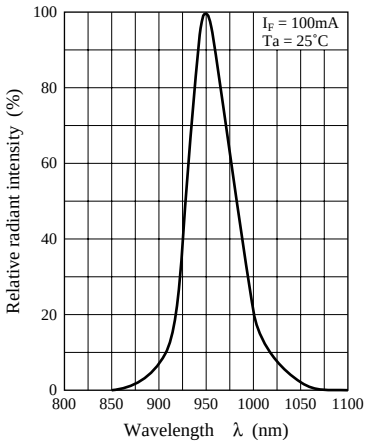
ΔP_O — Ta



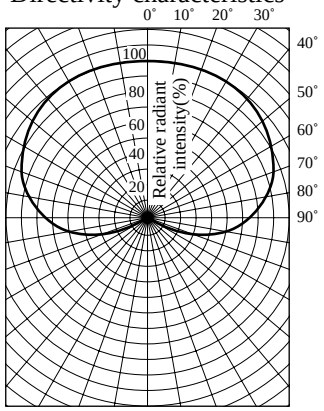
λ_P — Ta



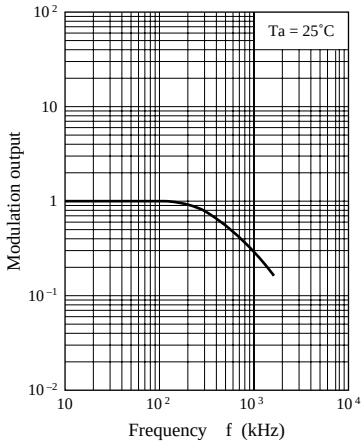
Spectral characteristics



Directivity characteristics



Frequency characteristics



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⚠ DANGER

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